

Amendments to the Claims.

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Claim 1 (currently amended): A single unitary layer of insulating material directly contacting and formed between conductive elements in an integrated circuit without other intervening materials, comprising a polysiloxane network consisting essentially of silicon, oxygen, carbon and hydrogen and incorporating carbon-silicon bonding and having a dielectric constant of less than about 3.3.

Claim 2 (original): The insulating material of Claim 1, having a dielectric constant of less than about 3.2.

Claim 3 (original): The insulating material of Claim 1, having a carbon content of between about 5% and 20% relative to a silicon content.

Claim 4 (original): The insulating material of Claim 1, wherein the conductive elements comprise metal runners.

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Claim 5 (currently amended): An integrated circuit, comprising:

a first conductive element providing a first electrical path of the circuit;

a second conductive element providing a second electrical path of the circuit, the second conductive element separated from the first conductive element by a gap; and

a unitary single insulating layer directly contacting the first and second conductive elements and sandwiched filling the gap between the first and second conductive elements, the insulating layer comprising polysiloxane, consisting essentially of silicon, oxygen, carbon and hydrogen and incorporating carbon therein and having a dielectric constant of less than about 3.5.

Claim 6 (original): The integrated circuit of Claim 5, wherein the insulating layer has a dielectric constant of less than about 3.3.

Claim 7 (original): The integrated circuit of Claim 6, wherein the first and second conductive elements are metal runners.

Claim 8 (original): The integrated circuit of Claim 6, wherein the first and second conductive elements are transistor active areas within a semiconductor substrate.

Claim 9 (original): The integrated circuit of Claim 8, wherein the insulating layer comprises a sidewall spacer.

Claim 10 (original): The integrated circuit of Claim 9, wherein the first conductive element is a transistor gate electrode and the second conductive element is a contact to a transistor active area.